

# PBSS4560PA

# 60 V, 6 A NPN low V<sub>CEsat</sub> (BISS) transistor Rev. 1 — 19 May 2010

Product data sheet

#### 1. **Product profile**

#### 1.1 General description

NPN low V<sub>CEsat</sub> Breakthrough In Small Signal (BISS) transistor, encapsulated in an ultra thin SOT1061 leadless small Surface-Mounted Device (SMD) plastic package with medium power capability.

PNP complement: PBSS5560PA.

#### 1.2 Features and benefits

- Low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability I<sub>C</sub> and I<sub>CM</sub>
- Smaller required Printed-Circuit Board (PCB) area than for conventional transistors
- Exposed heat sink for excellent thermal and electrical conductivity
- Leadless small SMD plastic package with medium power capability

## 1.3 Applications

- Loadswitch
- Battery-driven devices
- Power management
- Charging circuits
- Power switches (e.g. motors, fans)

### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{CEO}$	collector-emitter voltage	open base	-	-	60	V
I <sub>C</sub>	collector current		-	-	6	Α
I <sub>CM</sub>	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	-	7	Α
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_C = 6 \text{ A};$ $I_B = 300 \text{ mA}$	<u>[1]</u> -	34	48	mΩ

<sup>[1]</sup> Pulse test:  $t_p \le 300 \ \mu s; \ \delta \le 0.02.$ 



# 2. Pinning information

Table 2. Pinning

	•		
Pin	Description	Simplified outline	Graphic symbol
1	base		
2	emitter	3	3 
3	collector		1 —
		1 2	sym021
		Transparent top view	

# 3. Ordering information

Table 3. Ordering information

Type number	Package	Package				
	Name	Description	Version			
PBSS4560PA	HUSON3	plastic thermal enhanced ultra thin small outline package; no leads; three terminals; body 2 $\times$ 2 $\times$ 0.65 mm	SOT1061			

## 4. Marking

Table 4. Marking codes

Type number	Marking code
PBSS4560PA	A8

# 5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

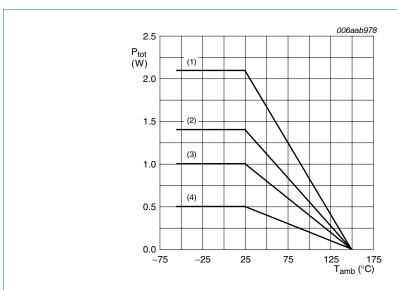
Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CBO}$	collector-base voltage	open emitter	-	60	V
$V_{CEO}$	collector-emitter voltage	open base	-	60	V
$V_{EBO}$	emitter-base voltage	open collector	-	6	V
I <sub>C</sub>	collector current		-	6	Α
I <sub>CM</sub>	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	7	Α
I <sub>B</sub>	base current		-	600	mA
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25  ^{\circ}C$	<u>[1]</u> -	500	mW
			[2] -	1	W
			[3] _	1.4	W
			[4] _	2.1	W

Table 5. Limiting values ... continued

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		-55	+150	°C
T <sub>stg</sub>	storage temperature		-65	+150	°C

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.
- [4] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.



- (1) Ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint
- (2) FR4 PCB, mounting pad for collector 6 cm<sup>2</sup>
- (3) FR4 PCB, mounting pad for collector 1 cm<sup>2</sup>
- (4) FR4 PCB, standard footprint

Fig 1. Power derating curves

## 6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$ thermal resistance from junction to ambient	in free air	<u>[1]</u> _	-	250	K/W	
		[2]	-	125	K/W	
			[3]	-	90	K/W
			[4]	-	60	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.
- B] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.
- [4] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.

PBSS4560PA

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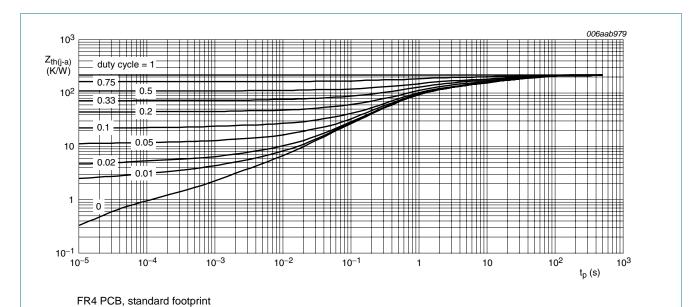


Fig 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

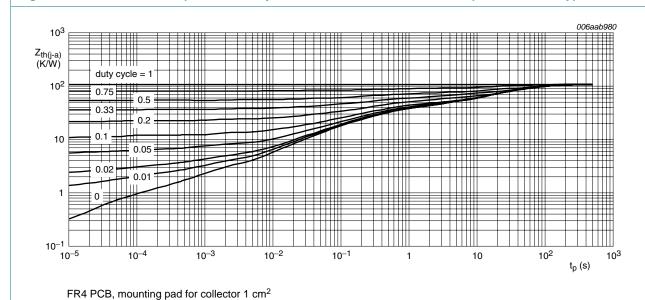


Fig 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

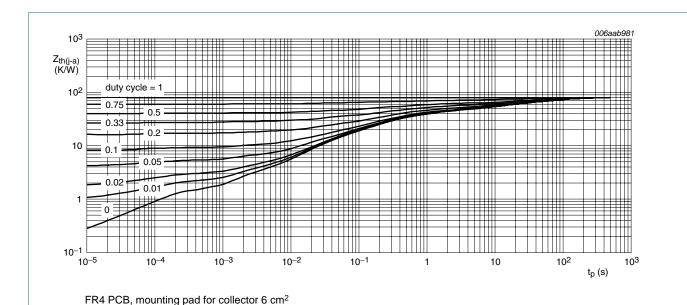
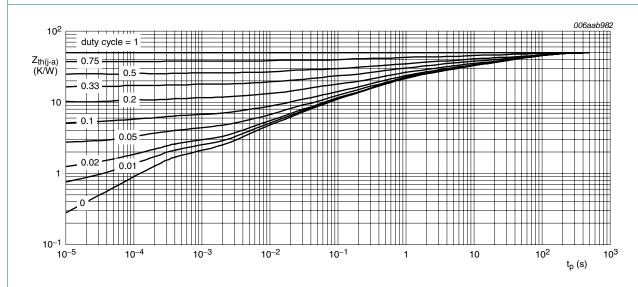


Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



Ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint

Fig 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

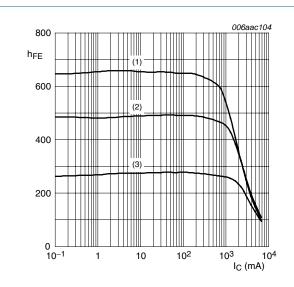
## 7. Characteristics

**Table 7. Characteristics** 

 $T_{amb} = 25$  °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base	$V_{CB} = 48 \text{ V}; I_E = 0 \text{ A}$	-	-	100	nΑ
	cut-off current	$V_{CB} = 48 \text{ V}; I_{E} = 0 \text{ A};$ $T_{j} = 150 \text{ °C}$	-	-	50	μА
I <sub>CES</sub>	collector-emitter cut-off current	$V_{CE} = 48 \text{ V}; V_{BE} = 0 \text{ V}$	-	-	100	nA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}$	-	-	100	nA
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = 2 V	[1]			
		$I_{\rm C} = 0.5  {\rm A}$	280	440	-	
		I <sub>C</sub> = 1 A	260	420	-	
		I <sub>C</sub> = 2 A	210	325	-	
		I <sub>C</sub> = 6 A	70	120	-	
V <sub>CEsat</sub>	collector-emitter	$I_C = 0.5 \text{ A}; I_B = 50 \text{ mA}$	[1] -	22	30	mV
	saturation voltage	$I_C = 1 A; I_B = 50 mA$	[1] -	45	60	mV
		$I_C = 1 A; I_B = 10 mA$	[1] -	70	95	mV
		$I_C = 2 \text{ A}; I_B = 20 \text{ mA}$	[1] -	115	170	mV
		$I_C = 3 A$ ; $I_B = 30 mA$	[1] -	165	250	mV
		$I_C = 4 A$ ; $I_B = 400 \text{ mA}$	[1] -	130	200	mV
		$I_C = 6 A$ ; $I_B = 300 mA$	[1] -	200	290	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_C = 6 \text{ A}; I_B = 300 \text{ mA}$	[1] -	34	48	mΩ
V <sub>BEsat</sub>	base-emitter	$I_C = 1 A; I_B = 10 mA$	[1] -	0.75	0.9	V
	saturation voltage	$I_C = 6 \text{ A}; I_B = 300 \text{ mA}$	[1] -	0.97	1.1	V
$V_{BEon}$	base-emitter turn-on voltage	$V_{CE} = 2 \text{ V}; I_{C} = 2 \text{ A}$	[1] -	0.75	0.9	V
t <sub>d</sub>	delay time	$V_{CC} = 9 \text{ V}; I_C = 2 \text{ A};$	-	22	-	ns
t <sub>r</sub>	rise time	$I_{Bon} = 0.1 \text{ A};$ $I_{Boff} = -0.1 \text{ A}$	-	101	-	ns
t <sub>on</sub>	turn-on time	I <sub>Boff</sub> = -0.1 A	-	123	-	ns
t <sub>s</sub>	storage time		-	635	-	ns
t <sub>f</sub>	fall time		-	145	-	ns
t <sub>off</sub>	turn-off time		-	780	-	ns
f⊤	transition frequency	$V_{CE} = 10 \text{ V};$ $I_{C} = 100 \text{ mA};$ $f = 100 \text{ MHz}$	90	150	-	MHz
C <sub>c</sub>	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz	-	23	30	pF

<sup>[1]</sup> Pulse test:  $t_p \le 300~\mu s;~\delta \le 0.02.$ 



- $V_{CE} = 2 V$
- (1) T<sub>amb</sub> = 100 °C
- (2)  $T_{amb} = 25 \, ^{\circ}C$
- (3)  $T_{amb} = -55 \, ^{\circ}C$

Fig 6. DC current gain as a function of collector current; typical values

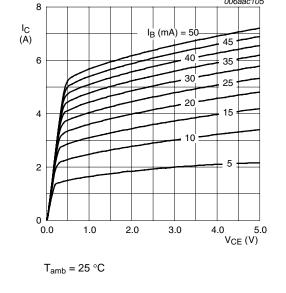
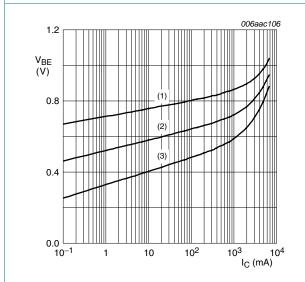
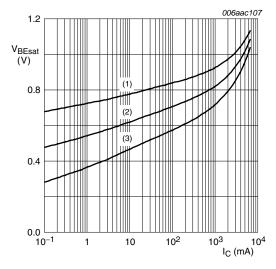


Fig 7. Collector current as a function of collector-emitter voltage; typical values



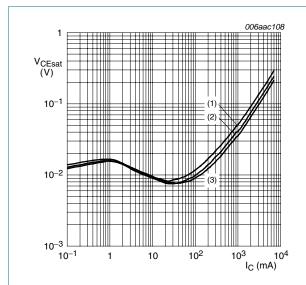
- $V_{CE} = 2 V$
- (1)  $T_{amb} = -55 \, ^{\circ}C$
- (2)  $T_{amb} = 25 \, ^{\circ}C$
- (3)  $T_{amb} = 100 \, ^{\circ}C$

Fig 8. Base-emitter voltage as a function of collector current; typical values



- $I_{\rm C}/I_{\rm B} = 20$
- (1)  $T_{amb} = -55 \, ^{\circ}C$
- (2)  $T_{amb} = 25 \, ^{\circ}C$
- (3)  $T_{amb} = 100 \, ^{\circ}C$

Fig 9. Base-emitter saturation voltage as a function of collector current; typical values



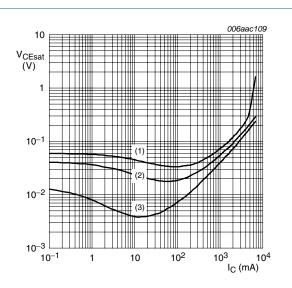
$$I_{\rm C}/I_{\rm B} = 20$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3)  $T_{amb} = -55 \, ^{\circ}C$ 

Fig 10. Collector-emitter saturation voltage as a function of collector current; typical values

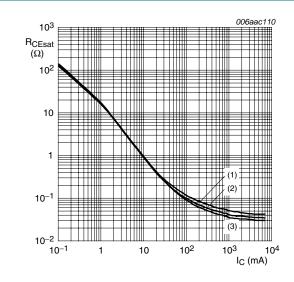


(1) 
$$I_C/I_B = 100$$

(2) 
$$I_C/I_B = 50$$

(3)  $I_C/I_B = 10$ 

Fig 11. Collector-emitter saturation voltage as a function of collector current; typical values



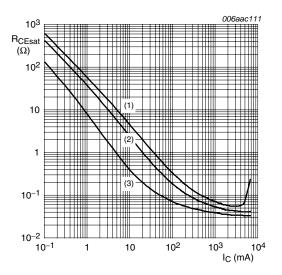
 $I_{\rm C}/I_{\rm B}=20$ 

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3)  $T_{amb} = -55 \, ^{\circ}C$ 

Fig 12. Collector-emitter saturation resistance as a function of collector current; typical values



T<sub>amb</sub> = 25 °C

(1) 
$$I_C/I_B = 100$$

(2)  $I_C/I_B = 50$ 

(3)  $I_C/I_B = 10$ 

Fig 13. Collector-emitter saturation resistance as a function of collector current; typical values

## 8. Test information

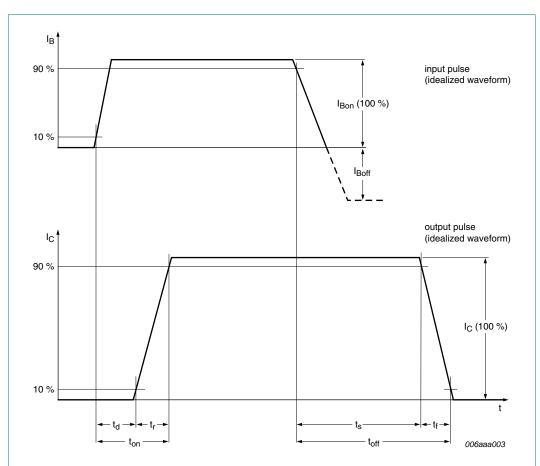
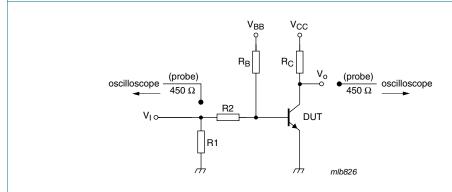
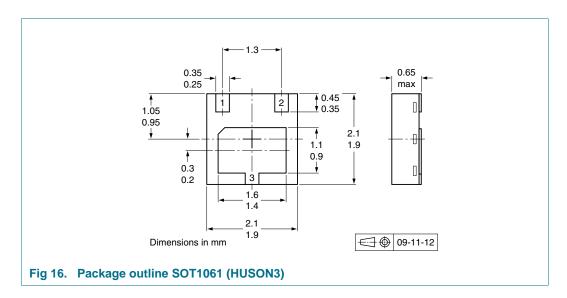


Fig 14. BISS transistor switching time definition



 $V_{CC}=9~V;~I_C=2~A;~I_{Bon}=0.1~A;~I_{Boff}=-0.1~A$  Fig 15. Test circuit for switching times

## 9. Package outline



# 10. Packing information

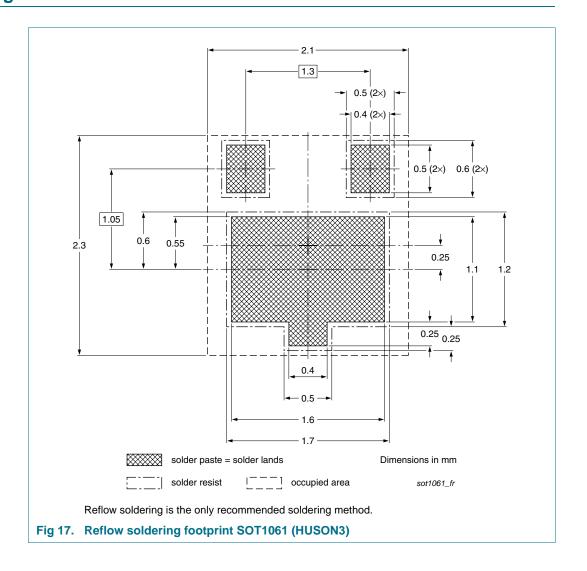
Table 8. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing quantity
			3000
PBSS4560PA	SOT1061	4 mm pitch, 8 mm tape and reel	-115

<sup>[1]</sup> For further information and the availability of packing methods, see Section 14.

# 11. Soldering





# 12. Revision history

### Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PBSS4560PA v.1	20100519	Product data sheet	-	-

## 13. Legal information

#### 13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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NXP Semiconductors PBSS4560PA

## 60 V, 6 A NPN low V<sub>CEsat</sub> (BISS) transistor

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# PBSS4560PA

## 60 V, 6 A NPN low V<sub>CEsat</sub> (BISS) transistor

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